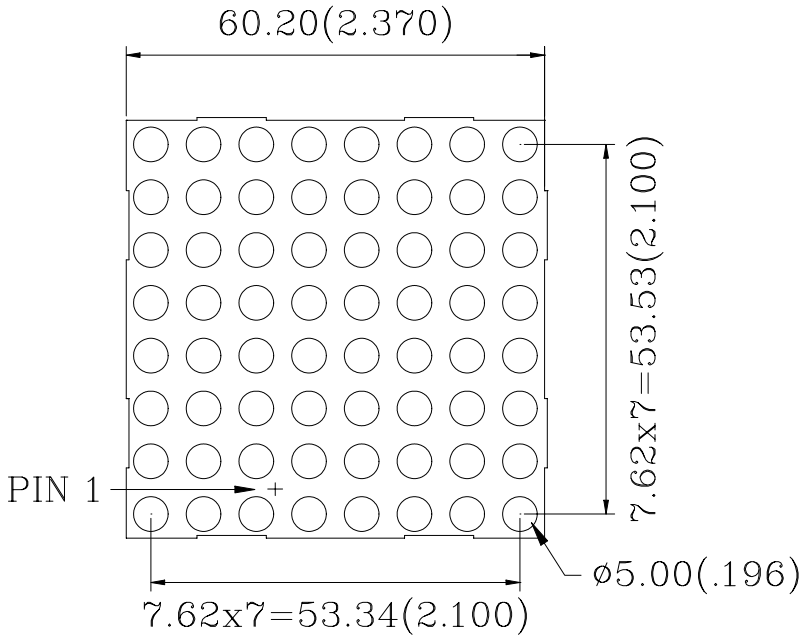
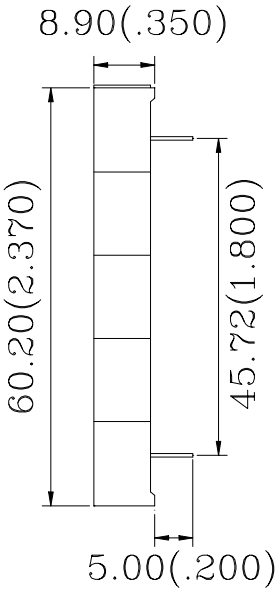
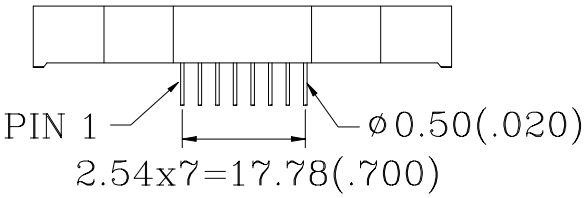
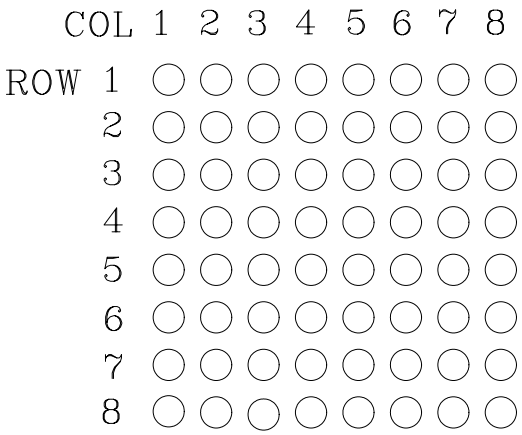
PACKAGE DIMENSIONS



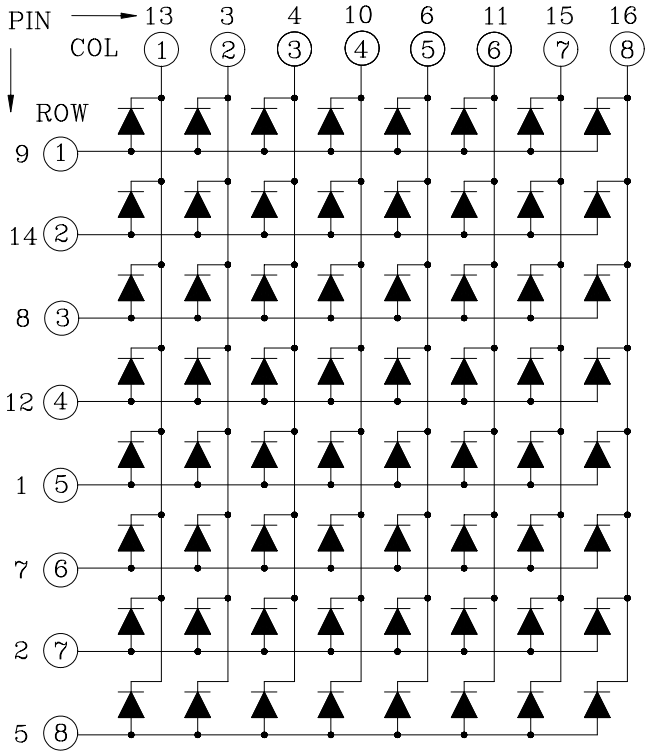






NOTES : 1. All dimensions are in millimeters. (inches)
2. Tolerance is ± 0.25(0.010") unless otherwise specified.

TYPICAL INTERNAL EGUIVALENT CIRCUIT



C-5880SR			
PIN NO	FUNCTION	PIN NO	FUNCTION
1	Anode Row 5	9	Anode Row 1
2	Anode Row 7	10	Cathode Column 4
3	Cathode Column 2	11	Cathode Column 6
4	Cathode Column 3	12	Anode Row 4
5	Anode Row 8	13	Cathode Column 1
6	Cathode Column 5	14	Anode Row 2
7	Anode Row 6	15	Cathode Column 7
8	Anode Row 3	16	Cathode Column 8

FEATURES

- ∗ 60.20mm (2.3 inch) MATRIX HEIGHT
- ∗ 8x8 ARRAY WITH X-Y SELECT
- ∗ LOW POWER , HIGH CONTRAST & BRIGHTNESS
- ∗ MATRIX ORIENTATION OF CATHODE COLUMN AND ANODE ROW
- ∗ STACKABLE VERTICAL AND HORIZONTAL

Raw Material : GaAlAs/GaAs

ABSOLUTE MAXIMUM RATING : (Ta = 25°C)

SYMBOL	PARAMETER	SUPER RED	UNIT
P_{AD}	Power Dissipation Per Dot	60	mW
V_R	Reverse Voltage Per Dot	5	V
I_{AF}	Continuous Forward Current Per Dot	25	mA
I_{PF}	Peak Forward Current Per Dice (Duty－0.1,1KHz)	100	mA
—	Derating Linear From 25°C Per Dot	0.33	mA/°C
Topr	Operating Temperature	－35°C to 85°C	
Tstg	Storage Temperature	－35°C to 85°C	
Solder Temperature 1/16 inch Below Seating Plane for 3 Seconds at 250°C			

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25°C)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V_F	Forward Voltage Per Dot	I_F = 20mA		1.8	2.4	V
I_R	Reverse Current	V_R = 5V			100	μA
λ_P	Peak Emission Wavelength	I_F = 20mA		660		nm
λ_D	Dominant Wavelength	I_F = 20mA		643		nm
$\Delta\lambda$	Spectral Line Half-Width	I_F = 20mA		20		nm
I_V	Luminous Intensity Per Dot	I_F = 10mA		20.0		mcd